

KSC3953

CRT Display Video Output

- High Current Gain Bandwidth Product : f_T=400MHz(Typ.)
- High Collector-Emitter Voltage: V_{CEO}=120V
 Low Reverse Transfer Capacitance: C_{re}=1.7pF(Typ.)



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	120	V
V _{CEO}	Collector-Emitter Voltage	120	V
V _{EBO}	Emitter-Base Voltage	3	V
I _C	Collector Current (DC)	200	mA
I _{CP}	Collector Current (Pulse)	400	mA
P _C	Collector Dissipation (T _a =25°C)	1.3	W
P _C	Collector Dissipation (T _C =25°C)	8	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu A, I_B = 0$	120			V
BV _{EBO}	Collector-Emitter Breakdown Voltage	$I_C = 1 \text{mA}, R_{BE} = \infty$	120			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	3			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 80V, I_{E} = 0$			0.1	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 2V, I_{C} = 0$			1.0	μΑ
h _{FE1}	DC Current Gain	$V_{CE} = 10V, I_{C} = 10mA$	40		120	
h _{FE2}		$V_{CE} = 10V, I_{C} = 100mA$	20			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 30 \text{mA}, I_B = 3 \text{mA}$			1.0	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 30$ mA, $I_B = 3$ mA			1.0	V
f _T	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 50mA$		400		MHz
C _{ob}	Output Capacitance	V _{CB} = 30V, f = 1MHz		2.1		pF
C _{re}	Reverse Transfer Capacitance	V _{CB} = 30V, f = 1MHz		1.7		pF

h_{FE} Classificntion

Classification	С	D
h _{FE1}	40 ~ 80	60 ~ 120

Typical Characteristics

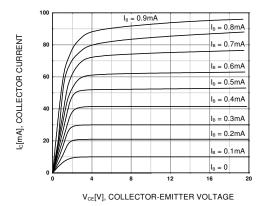


Figure 1. Static Characteristic

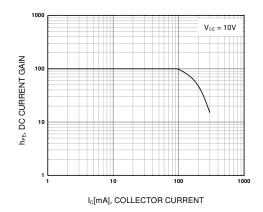


Figure 2. DC current Gain

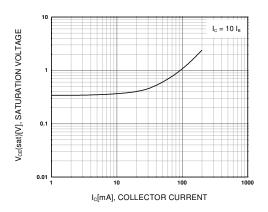


Figure 3. Collector-Emitter Saturation Voltage

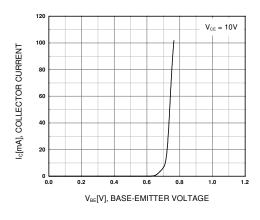


Figure 4. Base-Emitter On Voltage

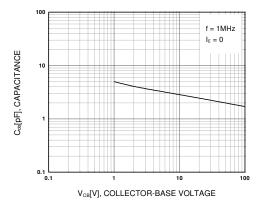


Figure 5. Collector Output Capacitance

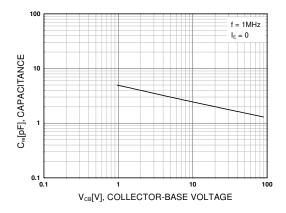


Figure 6. Reverse Capacitance

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Typical Characteristics (Continued)

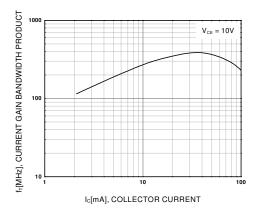


Figure 7. Current Gain Bandwidth Product

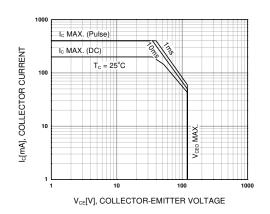


Figure 8. Safe Operating Area

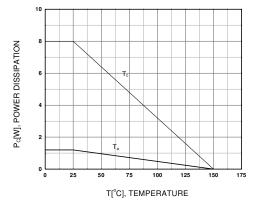


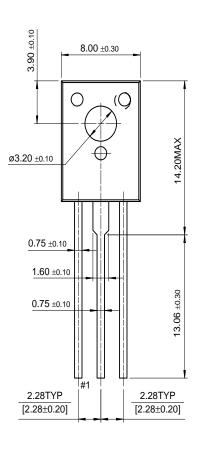
Figure 9. Power Derating

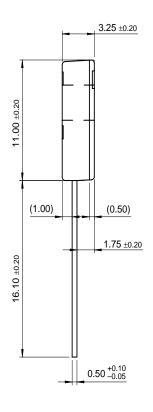
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Package Demensions

KSC3953

TO-126





Dimensions in Millimeters

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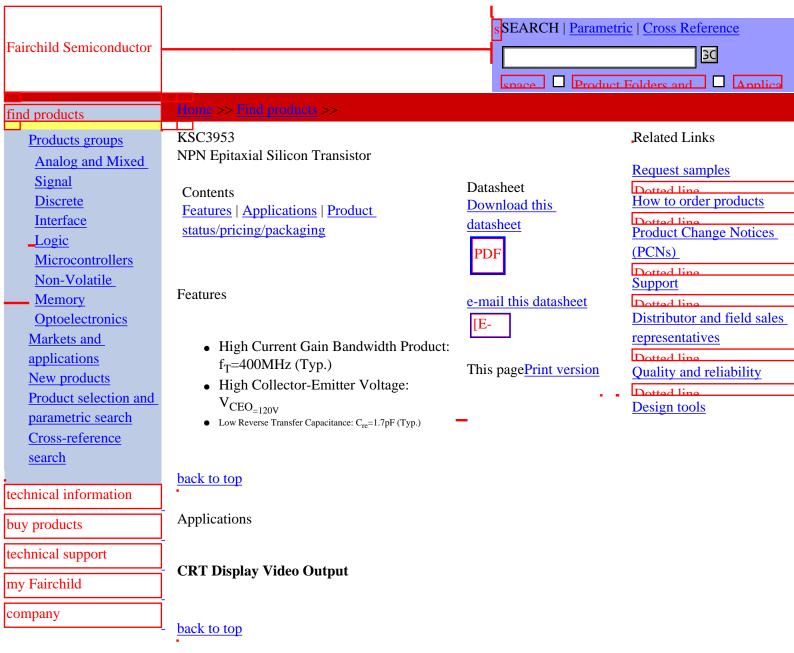
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Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
KSC3953DSTU	Full Production	\$0.164	<u>TO-126</u>	3	RAIL
KSC3953CS	Full Production	\$0.164	<u>TO-126</u>	3	BULK
KSC3953CSTU	Full Production	\$0.164	TO-126	3	RAIL

\$0.164

TO-126

3

BULK

Full Production

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KSC3953DS

^{* 1,000} piece Budgetary Pricing

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